NPN Silicon Power Transistor
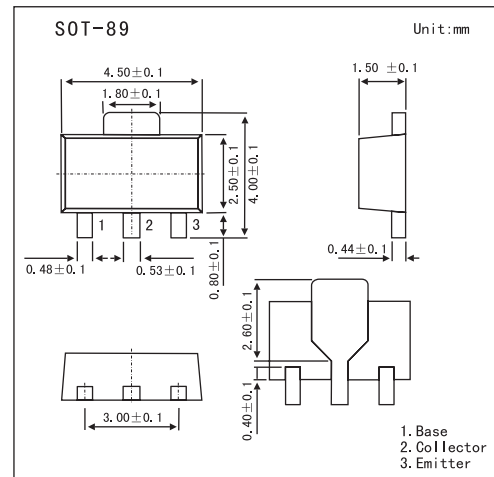
2SD882

■ Features

● Excellent hFE linearity and high hFE

  hFE = 60 to 400 (VCE = 2 V, IC = 1 A)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	VCBO	40	V
Collector to Emitter Voltage	VCEO	30	V
Emitter to Base Voltage	VEBO	6	V
Collector Current to Continuous	IC	3	A
Collector Dissipation	PC	0.5	W
Junction Temperature	TJ	150	℃
Storage Temperature	Tstg	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	VCBO	IC=100uA , IE=0	40			V
Collector-emitter breakdown voltage	VCEO	IC= 10 mA , IB=0	30			V
Emitter-base breakdown voltage	VEBO	IE= 100 uA , IC=0	6			V
Collector cut-off current	ICBO	VCB=40 V , IE=0			1	uA
Collector cut-off current	ICEO	VCE=30 V , IB=0			10	uA
Emitter cut-off current	IEBO	VEB=6V , IC=0			1	uA
DC current gain	hFE	VCE= 2V, IC= 1A	60		400	
		VCE=2V, IC= 100mA	32			
Collector-emitter saturation voltage	VCE(sat)	IC=2A, IB= 0.2A			0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=2A, IB= 0.2A			1.5	V
Transition frequency	f T	VCE=5 V, IC=0.1mA,f = 10MHz	50			MHz

■ hFE Classification

Rank	R	O	P	E
hFE	60～120	100～200	160～320	200～400